



SamHop Microelectronics Corp.

**STU/D334S**

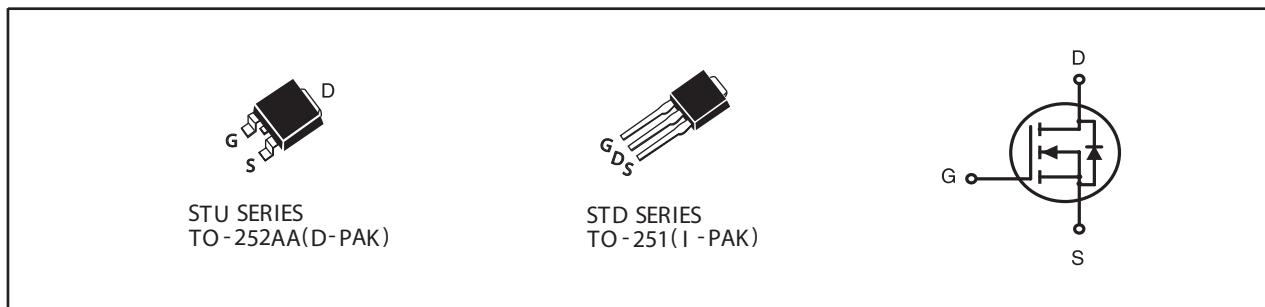
Ver 1.0

N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
VDSS	ID	RDS(ON) (mΩ) Max
30V	60A	4.7 @ VGS=10V
		6.8 @ VGS=4.5V

FEATURES

- Super high dense cell design for low RDS(ON).
- Rugged and reliable.
- TO-252 and TO-251 Package.



ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	$T_C=25^\circ\text{C}$	A
		$T_C=70^\circ\text{C}$	A
I_{DM}	-Pulsed ^a	176	A
E_{AS}	Single Pulse Avalanche Energy ^c	64	mJ
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	W
		$T_C=70^\circ\text{C}$	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	$^\circ\text{C/W}$

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ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
I _{DS}	Zero Gate Voltage Drain Current	V _{DS} =24V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1.0	1.6	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =30A		3.8	4.7	m ohm
		V _{GS} =4.5V , I _D =25A		5.1	6.8	m ohm
g _{FS}	Forward Transconductance	V _{DS} =10V , I _D =30A		64		S
DYNAMIC CHARACTERISTICS ^b						
C _{ISS}	Input Capacitance	V _{DS} =15V,V _{GS} =0V f=1.0MHz		2060		pF
C _{OSS}	Output Capacitance			323		pF
C _{RSS}	Reverse Transfer Capacitance			255		pF
SWITCHING CHARACTERISTICS ^b						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =15V I _D =1A V _{GS} =10V R _{GEN} = 6 ohm		31		ns
t _r	Rise Time			32		ns
t _{D(OFF)}	Turn-Off Delay Time			106		ns
t _f	Fall Time			17		ns
Q _g	Total Gate Charge	V _{DS} =15V,I _D =30A,V _{GS} =10V		29		nC
		V _{DS} =15V,I _D =30A,V _{GS} =4.5V		13.5		nC
Q _{gs}	Gate-Source Charge	V _{DS} =15V,I _D =30A, V _{GS} =10V		2.7		nC
Q _{gd}	Gate-Drain Charge			9		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V,I _s =6A		0.78	1.3	V
Notes						
a.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.						
b.Guaranteed by design, not subject to production testing.						
c.Starting T _J =25°C,L=0.5mH,V _{DD} = 20V.(See Figure13)						

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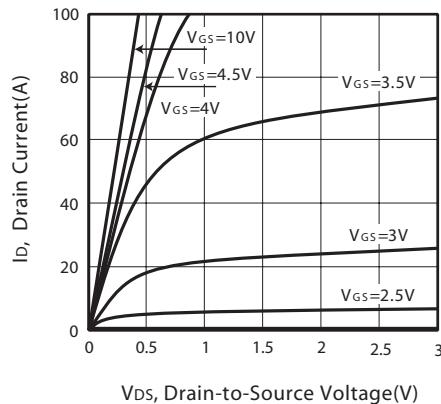


Figure 1. Output Characteristics

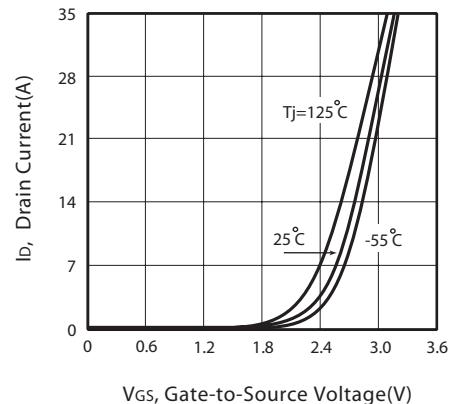


Figure 2. Transfer Characteristics

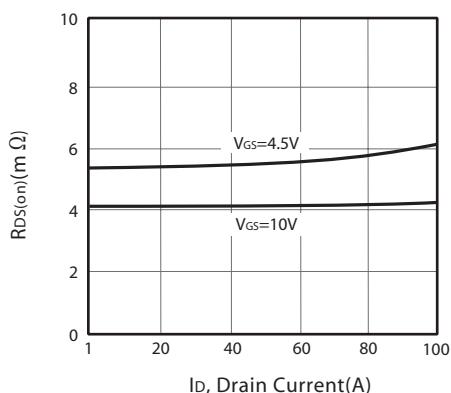


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

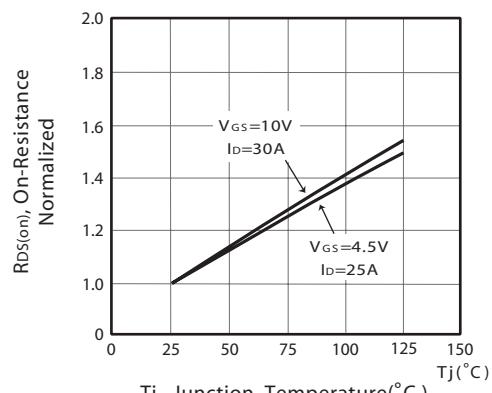


Figure 4. On-Resistance Variation with Drain Current and Temperature

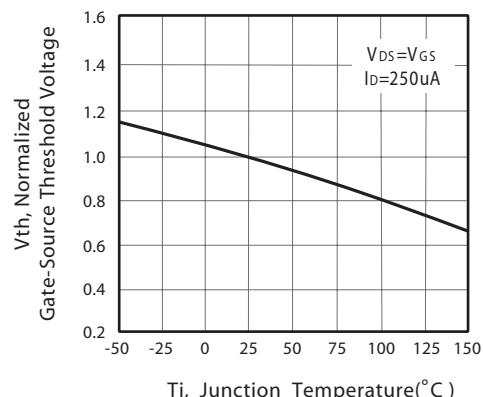


Figure 5. Gate Threshold Variation with Temperature

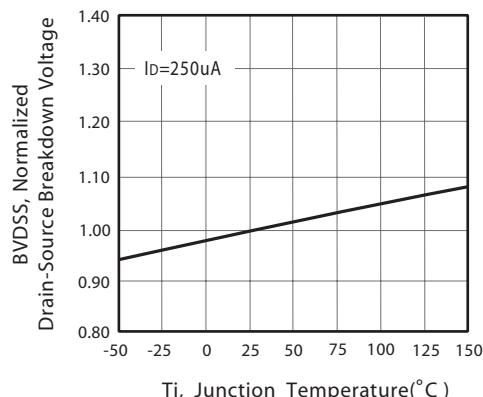
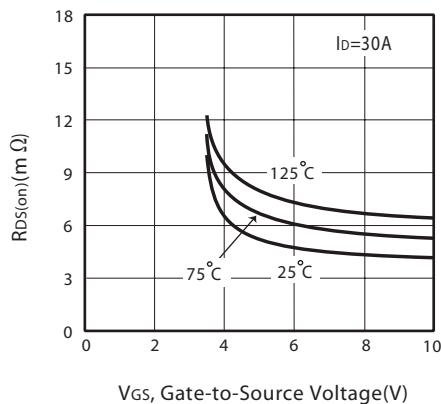


Figure 6. Breakdown Voltage Variation with Temperature

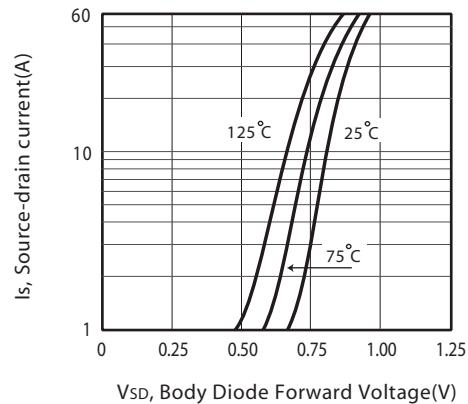
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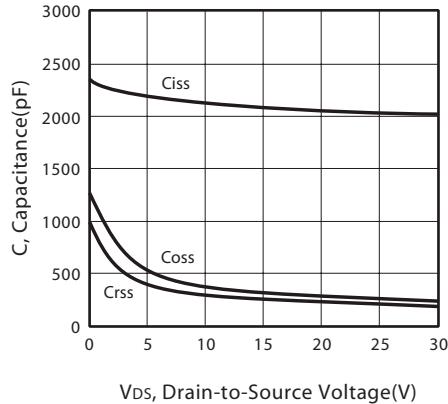
V_{GS}, Gate-to-Source Voltage(V)

Figure 7. On-Resistance vs. Gate-Source Voltage



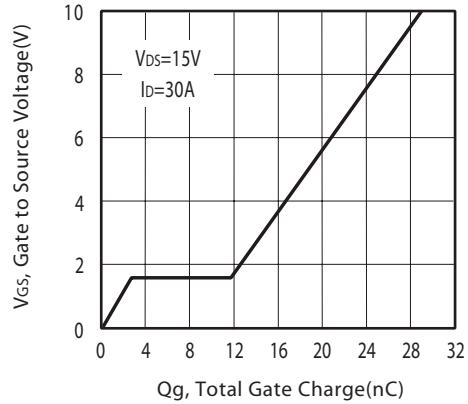
V_{SD}, Body Diode Forward Voltage(V)

Figure 8. Body Diode Forward Voltage Variation with Source Current



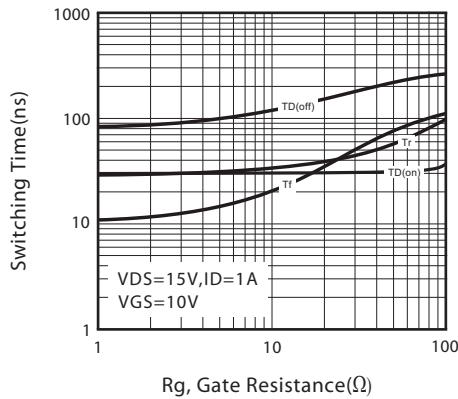
V_{DS}, Drain-to-Source Voltage(V)

Figure 9. Capacitance



Q_G, Total Gate Charge(nC)

Figure 10. Gate Charge



R_G, Gate Resistance(Ω)

Figure 11. switching characteristics

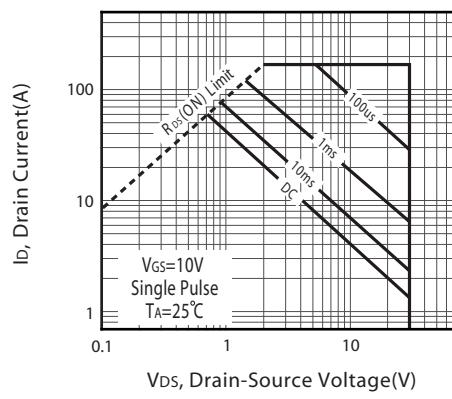
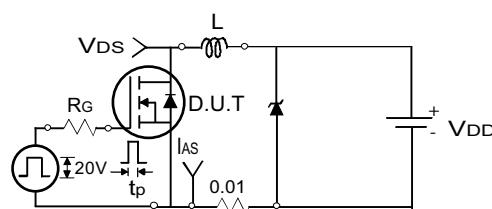


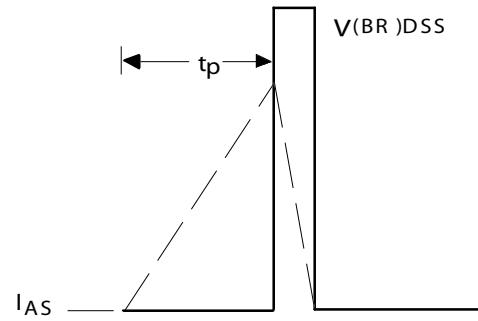
Figure 12. Maximum Safe Operating Area

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Uncamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

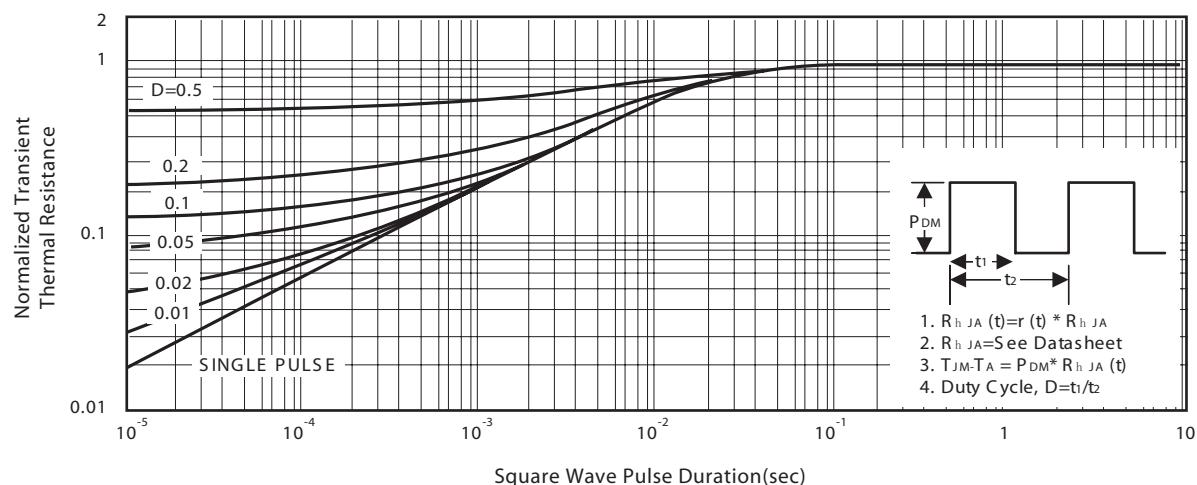
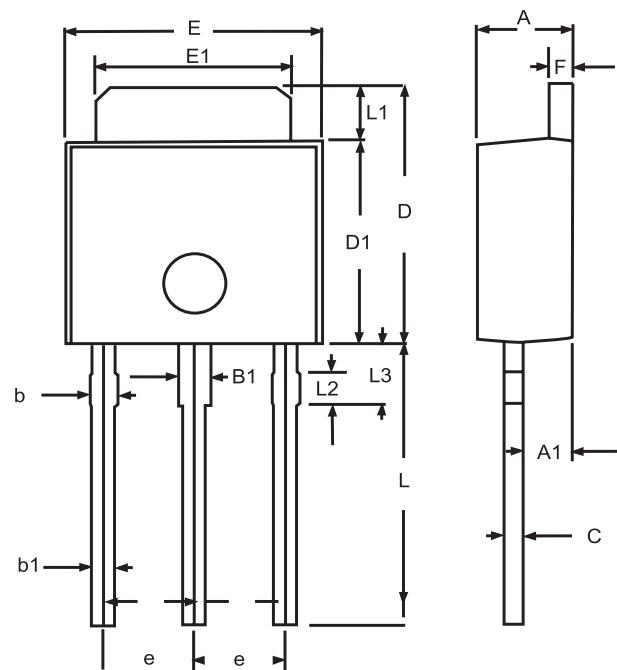


Figure 14. Normalized Thermal Transient Impedance Curve

PACKAGE OUTLINE DIMENSIONS

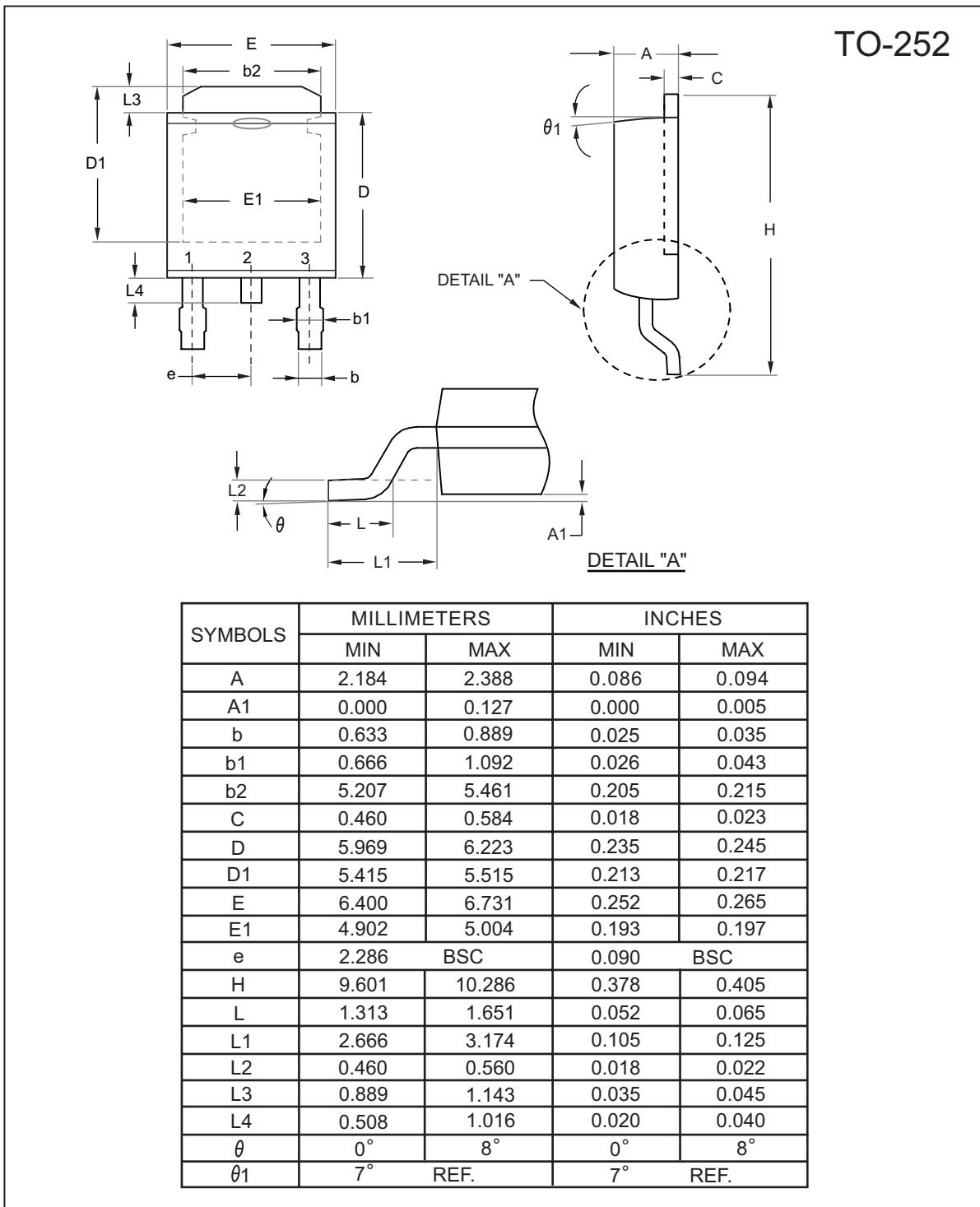
TO-251



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.40	0.087	0.095
A1	1.100	1.300	0.043	0.051
B1	0.650	1.050	0.026	0.041
b	0.500	0.900	0.020	0.035
b1	0.400	0.800	0.016	0.032
C	0.400	0.600	0.016	0.024
D	6.700	7.300	0.264	0.287
D1	5.400	5.650	0.213	0.222
E	6.40	6.650	0.252	0.262
e	2.100	2.500	0.083	0.098
F	0.400	0.600	0.016	0.024
L	7.000	8.000	0.276	0.315
L1	1.300	1.700	0.051	0.067
L2	0.700	0.900	0.028	0.035
L3	1.400	1.800	0.055	0.071

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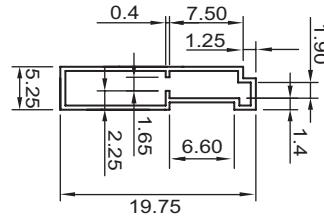
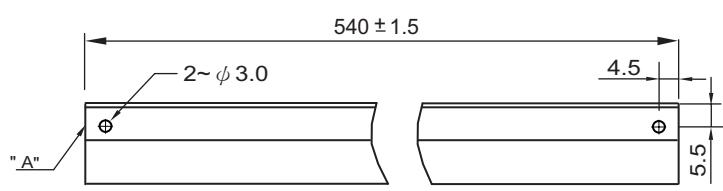
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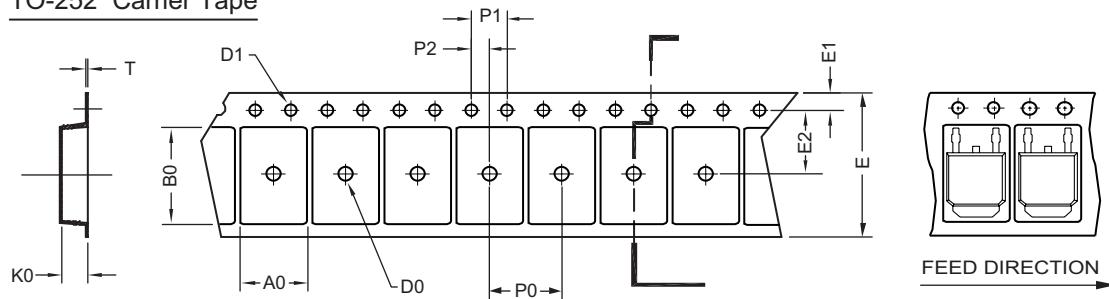
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TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



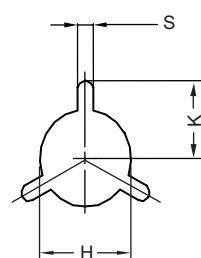
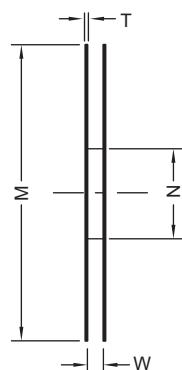
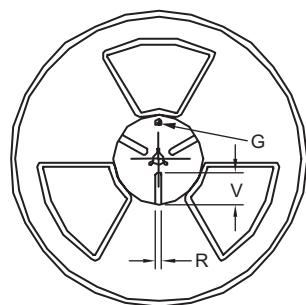
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ 2	φ 1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ± 0.5	---	---	---

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